#### Thyristors Datasheet

RoHS

Po

## MAC16CMG, MAC16CNG TRIAC – 400V - 800V



## **Additional Information**





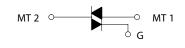


Samples

Resources

Accessories

#### **Functional Diagram**



## Description

Designed primarily for full wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full–wave, silicon gate–controlled devices are needed.

#### **Features**

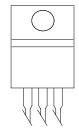
- High Commutating di/dt and High Immunity to dV/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability
   150 Amperes

#### Pin Out





- Glass Passivated Junctions for Reliability and Uniformity
- Operational in Three Quadrants, Q1, Q2, and Q3
- These Devices are Pb–Free and are RoHS Compliant





### Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1)MAC16CM(- 40 to 125°C)MAC16CN		V <sub>drm</sub> , V <sub>rrm</sub>	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 8$	I <sub>T (RMS)</sub>	16	A	
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)	I <sub>TSM</sub>	150	А	
Circuit Fusing Consideration ( $t = 8.3 \text{ ms}$ )		l²t	93	A <sup>2</sup> sec
Peak Gate Power (T <sub>c</sub> = 80°C, Pulse Width $\leq$ 1.0 µs)		P <sub>GM</sub>	20	W
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}C$ )		P <sub>G(AV)</sub>	0.5	W
Operating Junction Temperature Range		T,	-40 to +125	°C
Storage Temperature Range		T <sub>sta</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Recommended Operating Conditions may affect device reliability.
1. V<sub>DBM</sub> and V<sub>RBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

## **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 10 seconds	s, 1/8" from case for	TL	260	°C

# **Electrical Characteristics - OFF** ( $TJ = 25^{\circ}C$ unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.01	mA
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 125°C	I <sub>RRM</sub>	-	-	2.0	ШA

# **Electrical Characteristics - ON** ( $TJ = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 21$ A Peak)		V <sub>TM</sub>	_	1.2	1.6	V
Gate Trigger Current	MT2(+), G(+)		8.0	12	35	
(Continuous dc)	MT2(+), G(-)	Ι <sub>gt</sub>	8.0	16	35	mA
$(V_{\rm D} = 12 \text{ V}, \text{ R}_{\rm L} = 100 \Omega)$	MT2(-), G(-)		8.0	20	35	
Gate Trigger Voltage	MT2(+), G(+)		0.5	0.75	1.5	
(Continuous dc)	MT2(+), G(-)	V <sub>gt</sub>	0.5	0.72	1.5	V
$(V_{\rm D} = 12 \text{ V}, \text{ R}_{\rm L} = 100 \Omega)$	MT2(-), G(-)		0.5	0.82	1.5	
	MT2(+), G(+)		-	25	50	
Latching Current ( $V_p = 24 V$ , $I_c = 35 mA$ )	MT2(+), G(-)	I <sub>L</sub>	-	40	80	V
$(v_{\rm D} - 24, v_{\rm G} - 33, m_{\rm G})$	MT2(-), G(-)		_	24	50	
Holding Current ( $V_{D} = 12 V_{dc'}$ Gate Open, Initiating Current = ±150 mA)		I <sub>H</sub>	-	20	40	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Indicates Pulse Test: Pulse Width < 2.0 ms, Duty Cycle < 2%.



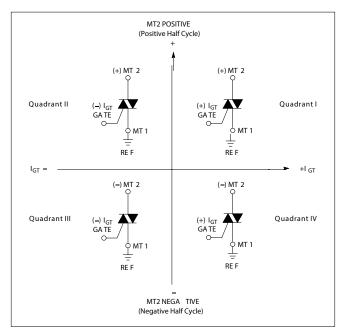
### **Dynamic Characteristics**

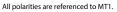
Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current ( $V_D = 400 V$ , $I_{TM} = 6.0 A$ , Commutating dV/dt = 24 V/µs, Gate Open, $T_J = 125^{\circ}C$ , f = 250 Hz, $C_L = 10 \mu$ F, $L_L = 40 m$ H, with Snubber)	(di/dt)c	15	-	-	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM'}$ Exponential Waveform, Gate Open, $T_J = 125^{\circ}C$ )	dv/dt	600	-	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 $\mu$ sec; diG/dt = 200 mA/ $\mu$ sec; f = 60 Hz	di/dt	-	-	10	

## **Voltage Current Characteristic of SCR**

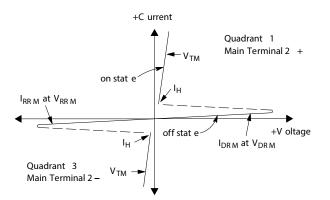
Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

## **Quadrant Definitions for a Triac**

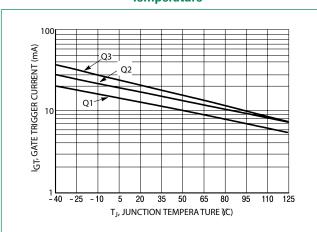




With in -phase signals (using standard AC lines) quadrants I and III are used

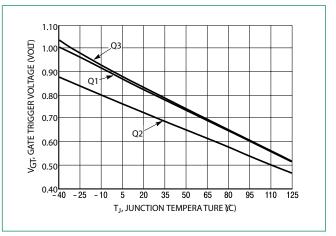






#### Figure 1. Typical Gate Trigger Current vs Junction Temperature

Figure 2. Typical Gate Trigger Voltage vs Junction Temperature



#### Figure 3. Typical Holding Current vs Junction Temperature

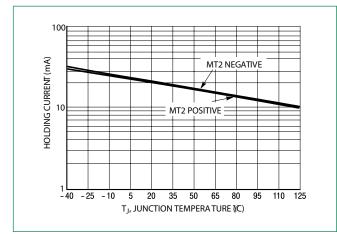


Figure 5. Typical RMS Current Derating

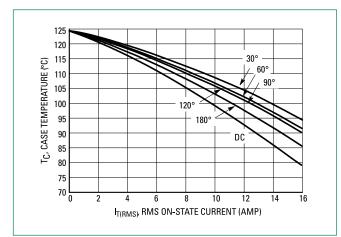


Figure 4. Typical Latching Current vs Junction Temperature

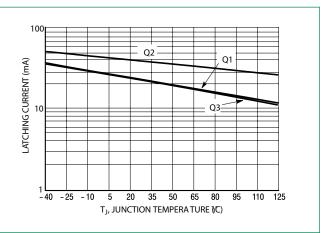
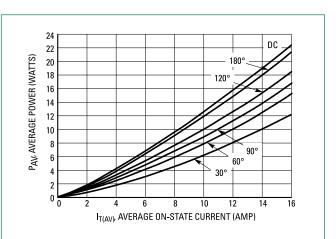
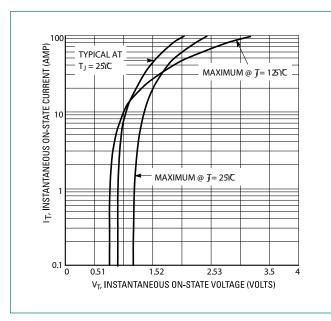


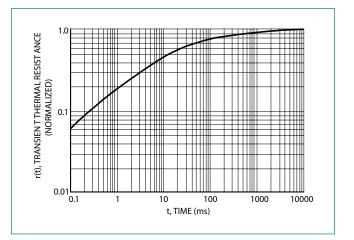
Figure 6. On-State Power Dissipation



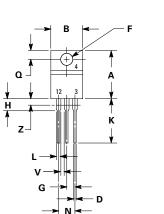
#### **Figure 7. On-State Characteristics**

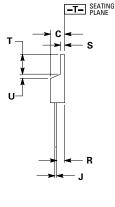


#### Figure 8. Typical Thermal Response

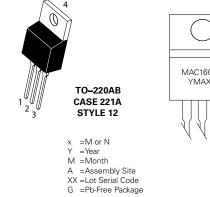


#### **Dimensions**





#### **Part Marking System**



$\bigcirc$
MAC16CxG YMAXX

Dim	Inc	hes	Millin	neters
Dim	Min	Мах	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
К	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
Ν	0.195	0.205	4.95	5.21
٥	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

## **Ordering Information**

Device	Package	Shipping
MAC16CMG	TO-220AB	1000 Units / Box
MAC16CNG	(Pb-Free)	1000 Units / Box

1. Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.

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